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(71)Applicant: SONY CORP

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(72)Inventor: HOSOMI MASAKATSU **MIZUGUCHI TETSUYA**

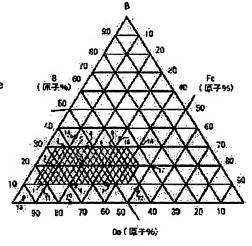
OBA KAZUHIRO BESSHO KAZUHIRO YAMAMOTO TETSUYA

KANO HIROSHI

(54) MAGNETORESISTIVE ELEMENT AND MAGNETIC MEMORY DEVICE (57)Abstract:

PROBLEM TO BE SOLVED: To simultaneously improve writing characteristics and reading characteristics by applying to a ferromagnetic layer a new material which has not been available heretofore.

SOLUTION: A magnetoresistive element comprises: a pair of the ferromagnetic layers opposed via an intermediate layer to obtain a magnetoresistance change by supplying current perpendicularly to a film surface. In this element, at least one of the magnetic layers contains a ferromagnetic material containing Fe, Co and B. The ferromagnetic material preferably contains FeaCobNicBd, wherein a, b, c and d each shows atomic %, 5≤a≤45, 35≤b≤85, 0<c≤35, and 10≤d≤30 are satisfied, and a+b+c+d=100 is satisfied.



LEGAL STATUS

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